EMH2408

ON Semiconductor®

N-Channel Power MOSFET 20V, 4A, 45mΩ, Dual EMH8

http://onsemi.com

Features

- The EMH2408 incorporates a N-channel MOSFET that feature low ON-resistance and ultrahigh-speed switching, thereby enabling high-density mounting
- 1.8V drive
- · Halogen free compliance

Specifications

Absolute Maximum Ratings at Ta=25°C

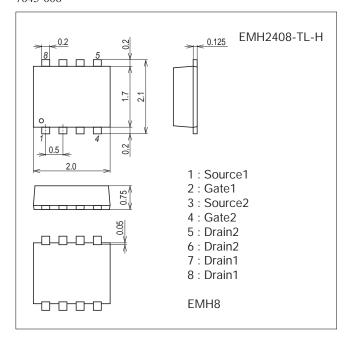
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	ID		4	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	16	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm) 1unit	1.0	W
Total Dissipation	PT	When mounted on ceramic substrate (900mm ² x0.8mm)	1.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

This product is designed to "ESD immunity < 200V*", so please take care when handling.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7045-006



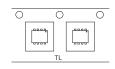
Product & Package Information

• Package : EMH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

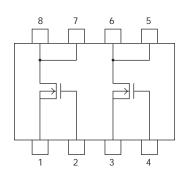
Packing Type: TL



Marking



Electrical Connection



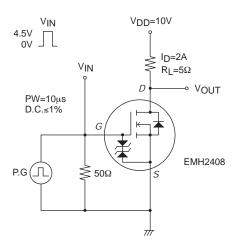
^{*} Machine Model

EMH2408

Electrical Characteristics at Ta=25°C

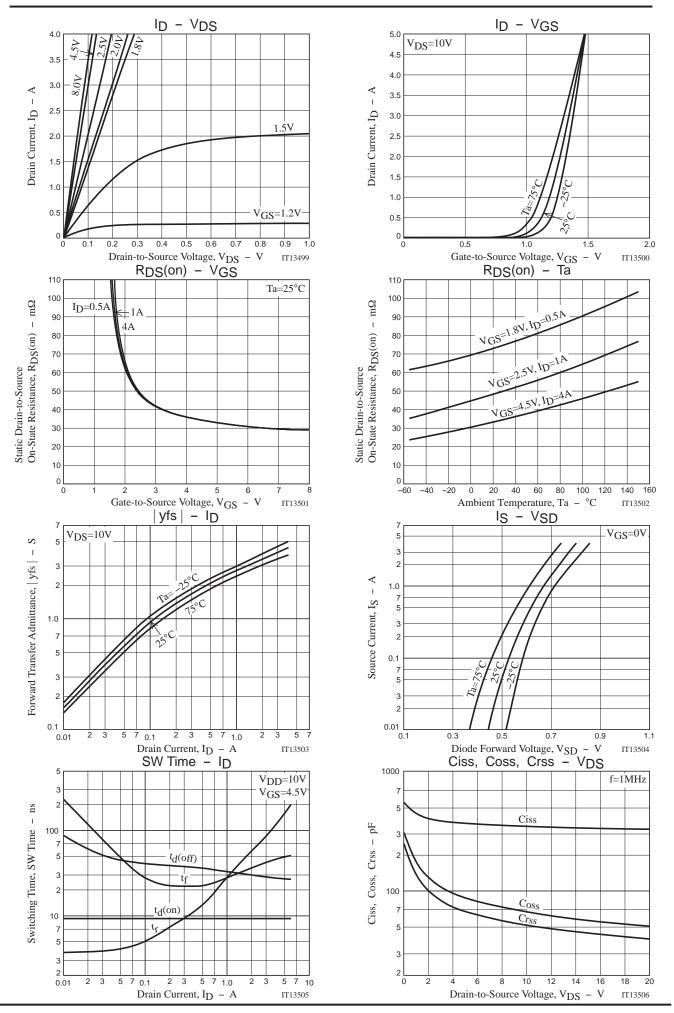
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Symbol		min	typ	max	Ullit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	0.4		1.3	٧	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =2A	2.0	3.4		S	
	R _{DS} (on)1	I _D =4A, V _G S=4.5V		34	45	mΩ	
static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =1A, V _{GS} =2.5V		49	67	mΩ	
	R _{DS} (on)3	I _D =0.5A, V _{GS} =1.8V		74	115	mΩ	
Input Capacitance	Ciss			345		pF	
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		67		pF	
Reverse Transfer Capacitance	Crss			52		pF	
Turn-ON Delay Time	t _d (on)			9.2		ns	
Rise Time	t _r	See specified Test Circuit.		60		ns	
Turn-OFF Delay Time	t _d (off)			30		ns	
Fall Time	tf			38		ns	
Total Gate Charge	Qg			4.7		nC	
Gate-to-Source Charge	Qgs V _D	V _{DS} =10V, V _{GS} =4.5V, I _D =4A		0.65		nC	
Gate-to-Drain "Miller" Charge	Qgd			1.6		nC	
Diode Forward Voltage	V _{SD}	I _S =4A, V _{GS} =0V		0.8	1.2	V	

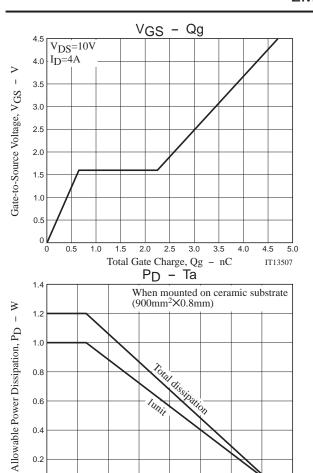
Switching Time Test Circuit



Ordering Information

Device			memo		
EMH2408-TL-H			Pb Free and Halogen Free		





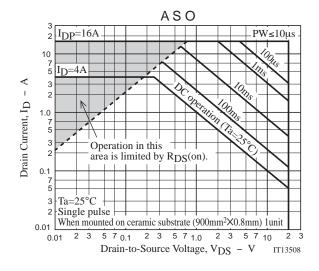
80

Ambient Temperature, Ta - °C

100

160

IT13509



0

0

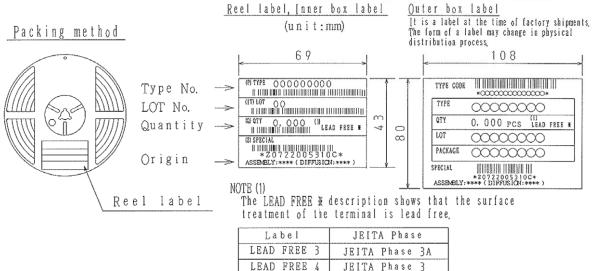
20

Embossed Taping Specification

EMH2408-TL-H

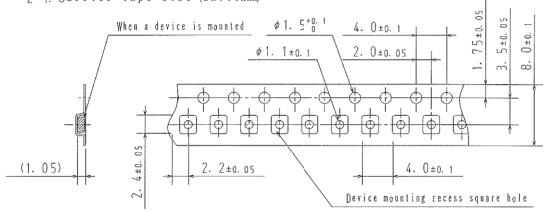
1. Packing Format

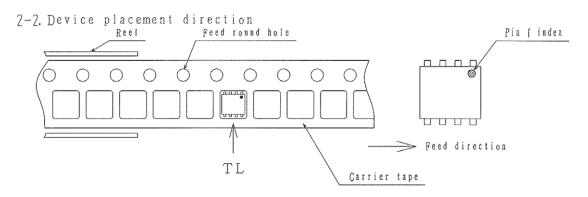
	Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
		Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
	EMH8	MCP4	3, 000	15, 000	90, 000	5 reels contained	6 inner boxes contained	
-						Dinensions:mm (external)	Dimensions:mm (external)	
-						183×72×185	440×195×210	



2. Taping configuration

7-1. Carrier tape size (unit:mm)

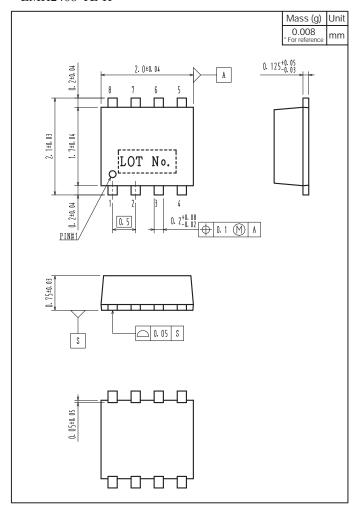




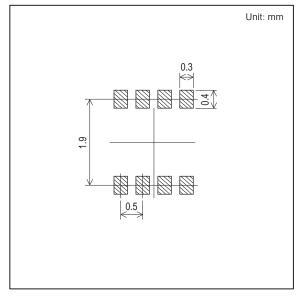
Those with pin 1 index on the feed hole side·····TL

Outline Drawing

EMH2408-TL-H



Land Pattern Example



Note on usage: Since the EMH2408 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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